

Ian M Povey

List of Publications by Year in descending order

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151
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151
docs citations

151
times ranked

3843
citing authors

#	ARTICLE	IF	CITATIONS
1	A multi-purpose pilot-scale molten metal & molten salt pyrolysis reactor. <i>MethodsX</i> , 2022, 9, 101606.	0.7	2
2	Combinatorial ALD for the growth of ZnO/TiO ₂ nanolaminates and mixed ZnO/TiO ₂ nanostructured films. <i>Materials Advances</i> , 2022, 3, 2896-2907.	2.6	8
3	Multifunctionalities of 2D MoS ₂ self-switching diode as memristor and photodetector. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2021, 126, 114451.	1.3	15
4	Structural and Electronic Properties of Polycrystalline InAs Thin Films Deposited on Silicon Dioxide and Glass at Temperatures below 500 Å°C. <i>Crystals</i> , 2021, 11, 160.	1.0	3
5	A Slot-Die Technique for the Preparation of Continuous, High-Area, Chitosan-Based Thin Films. <i>Polymers</i> , 2021, 13, 1566.	2.0	3
6	Structural and electrical characterisation of PtS from H ₂ S-converted Pt. <i>Applied Materials Today</i> , 2021, 25, 101163.	2.3	7
7	Large-area growth of MoS ₂ at temperatures compatible with integrating back-end-of-line functionality. <i>2D Materials</i> , 2021, 8, 025008.	2.0	14
8	Chemical Vapor Deposition of MoS ₂ for Back-End-of-Line Applications. <i>ECS Meeting Abstracts</i> , 2021, MA2021-02, 1952-1952.	0.0	0
9	Reconfigurable horizontal-vertical carrier transport in graphene/HfZrO field-effect transistors. <i>Nanotechnology</i> , 2020, 31, 025203.	1.3	1
10	MoS ₂ radio: detecting radio waves with a two-dimensional transition metal dichalcogenide semiconductor. <i>Nanotechnology</i> , 2020, 31, 06LT01.	1.3	10
11	Microwave applications of zirconium-doped hafnium oxide ferroelectrics: from nanoscale calculations up to experimental results. , 2020, , .		2
12	Next generation low temperature polycrystalline materials for above IC electronics. High mobility n- and p-type III-V metalorganic vapour phase epitaxy thin films on amorphous substrates. <i>JPhys Photonics</i> , 2020, 2, 025003.	2.2	4
13	One-Pot Synthesis of Co(OH) ₂ and/or Co ₃ O ₄ Decorated Cobalt-Doped ZnO Nanorod Arrays and Their Potential as (Photo)Anode Materials. <i>ChemistrySelect</i> , 2019, 4, 5033-5043.	0.7	0
14	ZnO Nanorod-Arrays as Photo-(Electro)Chemical Materials: Strategies Designed to Overcome the Material's Natural Limitations. <i>Journal of the Electrochemical Society</i> , 2018, 165, H3034-H3044.	1.3	6
15	Zinc oxide for solar water splitting: A brief review of the material's challenges and associated opportunities. <i>Nano Energy</i> , 2018, 54, 409-428.	8.2	126
16	Harvesting Electromagnetic Energy in the \sqrt{V} -Band Using a Rectenna Formed by a Bow Tie Integrated With a 6-nm-Thick Au/HfO ₂ /Pt Metal-Insulator-Metal Diode. <i>IEEE Transactions on Electron Devices</i> , 2018, 65, 2973-2980.	1.6	26
17	Aluminum Interdiffusion into LiCoO ₂ Using Atomic Layer Deposition for High Rate Lithium Ion Batteries. <i>ACS Applied Energy Materials</i> , 2018, 1, 3277-3282.	2.5	22
18	Atomic Layer Deposited Electron Transport Layers in Efficient Organometallic Halide Perovskite Devices. <i>MRS Advances</i> , 2018, 3, 3075-3084.	0.5	8

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19	2.55ÅGHz miniaturised phased antenna array based on 7Ånm thick Hf _x Zr _{1-x} O ₂ ferroelectrics. Electronics Letters, 2018, 54, 469-470.	0.5	15
20	Wafer-scale very large memory windows in graphene monolayer/HfZrO ferroelectric capacitors. Nanotechnology, 2018, 29, 425204.	1.3	15
21	Current rectification effects in 6Ånm thick Hf _{1-x} Zr _x O ₂ ferroelectrics/Si planar heterostructures. Physica E: Low-Dimensional Systems and Nanostructures, 2018, 104, 241-246.	1.3	2
22	Growth of V ₂ O ₅ Films for Battery Applications by Pulsed Chemical Vapor Deposition. ECS Transactions, 2018, 85, 83-94.	0.3	0
23	Effect of Surface and Defect Chemistry on the Photocatalytic Properties of Intentionally Defect-Rich ZnO Nanorod Arrays. ACS Applied Materials & Interfaces, 2018, 10, 17994-18004.	4.0	33
24	Electromagnetic energy harvesting based on HfZrO tunneling junctions. Nanotechnology, 2018, 29, 445203.	1.3	6
25	Inversion in the In _{0.53} Ga _{0.47} As metal-oxide-semiconductor system: Impact of the In _{0.53} Ga _{0.47} As doping concentration. Applied Physics Letters, 2017, 110, 032902.	1.5	5
26	Rapid low-temperature solution growth of ZnO:Co nanorod arrays with controllable visible light absorption. CrystEngComm, 2017, 19, 1938-1946.	1.3	10
27	The impact of forming gas annealing on the electrical characteristics of sulfur passivated Al ₂ O ₃ /In _{0.53} Ga _{0.47} As (110) metal-oxide-semiconductor capacitors. Applied Physics Letters, 2017, 110, 142905.	1.5	19
28	Defect-promoted photo-electrochemical performance enhancement of orange-luminescent ZnO nanorod-arrays. Physical Chemistry Chemical Physics, 2017, 19, 12255-12268.	1.3	33
29	Examining the relationship between capacitance-voltage hysteresis and accumulation frequency dispersion in InGaAs metal-oxide-semiconductor structures based on the response to post-metal annealing. Microelectronic Engineering, 2017, 178, 204-208.	1.1	20
30	(Invited) Tailoring Zinc Oxide Nanorod-Arrays for Photo-(electro)Chemical Applications. ECS Transactions, 2017, 77, 43-60.	0.3	1
31	Island Coalescence during Film Growth: An Underestimated Limitation of Cu ALD. Advanced Materials Interfaces, 2017, 4, 1700274.	1.9	18
32	Hall-effect mobility for a selection of natural and synthetic 2D semiconductor crystals. , 2017, , .		2
33	Very large phase shift of microwave signals in a 6 nm Hf _x Zr _{1-x} O ₂ ferroelectric at ±3 V. Nanotechnology, 2017, 28, 38LT04.	1.3	32
34	Lithographically Defined, Room Temperature Low Threshold Subwavelength Red-Emitting Hybrid Plasmonic Lasers. Nano Letters, 2016, 16, 7822-7828.	4.5	23
35	Back-gated Nb-doped MoS ₂ junctionless field-effect-transistors. AIP Advances, 2016, 6, .	0.6	20
36	Air sensitivity of MoS ₂ , MoSe ₂ , MoTe ₂ , HfS ₂ , and HfSe ₂ . Journal of Applied Physics, 2016, 120, .	1.1	134

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37	Band offsets and trap-related electron transitions at interfaces of (100)InAs with atomic-layer deposited Al ₂ O ₃ . Journal of Applied Physics, 2016, 120, 235701.	1.1	5
38	Progression towards high efficiency perovskite solar cells via optimisation of the front electrode and blocking layer. Journal of Materials Chemistry C, 2016, 4, 11269-11277.	2.7	17
39	The role of local chemical hardness and van der Waals interactions in the anionic polymerization of alkyl cyanoacrylates. Polymer Chemistry, 2016, 7, 3236-3243.	1.9	7
40	Capacitive behavior of Ag doped V ₂ O ₅ grown by aerosol assisted chemical vapour deposition. Electrochimica Acta, 2016, 196, 294-299.	2.6	41
41	Atomic Layer Deposition on Fabrics for Flame Resistance. ECS Transactions, 2015, 66, 31-35.	0.3	0
42	Indium Tin Oxide - Silicon Nanocrystal Nanocomposite Grown by Aerosol-Assisted Chemical Vapour Deposition. ECS Transactions, 2015, 66, 17-21.	0.3	0
43	Influence of Substrate on Hafnium Silicate Metal-Insulator-Metal Capacitors Grown by Atomic Layer Deposition. ECS Transactions, 2015, 66, 269-275.	0.3	0
44	A study of capacitance-voltage hysteresis in the HfO ₂ /InGaAs metal-oxide-semiconductor system. Microelectronic Engineering, 2015, 147, 273-276.	1.1	12
45	Electrochemical evaluation of vanadium pentoxide coatings grown by AACVD. Solar Energy Materials and Solar Cells, 2015, 143, 601-605.	3.0	11
46	Indium tin oxide-silicon nanocrystal nanocomposite grown by aerosol assisted chemical vapour deposition. Journal of Sol-Gel Science and Technology, 2015, 73, 666-672.	1.1	3
47	Effect of forming gas annealing on the inversion response and minority carrier generation lifetime of n and p-In _{0.53} Ga _{0.47} As MOS capacitors. Microelectronic Engineering, 2015, 147, 325-329.	1.1	4
48	High aspect ratio iridescent three-dimensional metal-insulator-metal capacitors using atomic layer deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2015, 33, .	0.9	14
49	Junctionless nanowire transistor fabricated with high mobility Ge channel. Physica Status Solidi - Rapid Research Letters, 2014, 8, 65-68.	1.2	16
50	Capacitance and Conductance for an MOS System in Inversion, with Oxide Capacitance and Minority Carrier Lifetime Extractions. IEEE Transactions on Electron Devices, 2014, 61, 4176-4185.	1.6	11
51	Diffusion of In _{0.53} Ga _{0.47} As elements through hafnium oxide during post deposition annealing. Applied Physics Letters, 2014, 104, .	1.5	23
52	A combined capacitance-voltage and hard x-ray photoelectron spectroscopy characterisation of metal/Al ₂ O ₃ /In _{0.53} Ga _{0.47} As capacitor structures. Journal of Applied Physics, 2014, 116, 024104.	1.1	2
53	Low sheet resistance titanium nitride films by low-temperature plasma-enhanced atomic layer deposition using design of experiments methodology. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2014, 32, 031506.	0.9	24
54	Electrical and physical characterization of the Al ₂ O ₃ /p-GaSb interface for 1%, 5%, 10%, and 22% (NH ₄) ₂ S surface treatments. Applied Physics Letters, 2014, 105, 162907.	1.5	18

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55	A bottom-up fabrication method for the production of visible light active photonic crystals. Journal of Materials Chemistry C, 2014, 2, 1675-1682.	2.7	9
56	Role of Interfacial Aluminum Silicate and Silicon as Barrier Layers for Atomic Layer Deposition of Al ₂ O ₃ Films on Chemically Cleaned InP(100) Surfaces. Journal of Physical Chemistry C, 2014, 118, 29164-29179.	1.5	5
57	Surface Oxide Characterization and Interface Evolution in Atomic Layer Deposition of Al ₂ O ₃ on InP(100) Studied by in Situ Infrared Spectroscopy. Journal of Physical Chemistry C, 2014, 118, 5862-5871.	1.5	16
58	Atomic layer deposition of Cu with a carbene-stabilized Cu(<i>scpi</i>) silylamide. Journal of Materials Chemistry C, 2014, 2, 9205-9214.	2.7	16
59	A study of capacitance-voltage hysteresis in HfO ₂ /InGaAs metal-oxide-semiconductor systems. , 2014, , .		1
60	Electrically active interface defects in the In _{0.53} Ga _{0.47} As MOS system. Microelectronic Engineering, 2013, 109, 182-188.	1.1	22
61	Plasma enhanced atomic layer deposition of copper: A comparison of precursors. Surface and Coatings Technology, 2013, 230, 3-12.	2.2	17
62	The Characterization and Passivation of Fixed Oxide Charges and Interface States in the Al ₂ O ₃ /InGaAs MOS System. IEEE Transactions on Device and Materials Reliability, 2013, 13, 429-443.	1.5	43
63	Junctionless InGaAs MOSFETs with InAlAs barrier isolation and channel thinning by digital wet etching. , 2013, , .		5
64	Investigation of electron mobility in surface-channel Al ₂ O ₃ /In _{0.53} Ga _{0.47} As MOSFETs. Solid-State Electronics, 2013, 88, 37-42.	0.8	6
65	Silicon nanocrystals: Novel synthesis routes for photovoltaic applications. Physica Status Solidi (A) Applications and Materials Science, 2013, 210, 649-657.	0.8	8
66	Effects of alternating current voltage amplitude and oxide capacitance on mid-gap interface state defect density extractions in In _{0.53} Ga _{0.47} As capacitors. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2013, 31, 01A119.	0.6	5
67	Electrical Properties and Charge Transport in the Pd/Al ₂ O ₃ /InGaAs MOS Structure. ECS Transactions, 2013, 58, 379-384.	0.3	0
68	X-ray optics developments at ESA. , 2013, , .		4
69	An investigation of capacitance-voltage hysteresis in metal/high- <i>k</i> /In _{0.53} Ga _{0.47} As metal-oxide-semiconductor capacitors. Journal of Applied Physics, 2013, 114, .	1.1	58
70	Nonhomogeneous spatial distribution of filamentary leakage current paths in circular area Pt/HfO ₂ /Pt capacitors. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2013, 31, 01A107.	0.6	9
71	Scalable high- <i>k</i> metal-insulator-metal capacitors with low leakage, high breakdown fields and improved voltage linearity. Electronics Letters, 2012, 48, 230.	0.5	1
72	(Invited) Can Metal/Al ₂ O ₃ /In _{0.53} Ga _{0.47} As/InP MOSCAP Properties Translate to Metal/Al ₂ O ₃ /In _{0.53} Ga _{0.47} As/InP MOSFET Characteristics. ECS Transactions, 2012, 45, 79-88.	0.3	1

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73	Uniform coating of high aspect ratio surfaces through atomic layer deposition. , 2012, , .		1
74	Observation of peripheral charge induced low frequency capacitance-voltage behaviour in metal-oxide-semiconductor capacitors on Si and GaAs substrates. Journal of Applied Physics, 2012, 111, .	1.1	19
75	Study of interface and oxide defects in high-k/ $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ n-MOSFETs. , 2012, , .		1
76	Improved reliability of $\text{Al}_2\text{O}_3/\text{InGaAs}/\text{InP}$ MOS structures through in-situ forming gas annealing. , 2012, , .		2
77	Impact of Forming Gas Annealing on the Performance of Surface-Channel $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ MOSFETs With an ALD Al_2O_3 Gate Dielectric. IEEE Transactions on Electron Devices, 2012, 59, 1084-1090.	1.6	52
78	Non-Covalent Functionalization of Graphene Using Self-Assembly of Alkane Amines. Advanced Functional Materials, 2012, 22, 717-725.	7.8	73
79	Analysis of the minority carrier response of <i>n</i> -type and <i>p</i> -type $\text{Au}/\text{Ni}/\text{Al}_2\text{O}_3/\text{In}_{0.53}\text{Ga}_{0.47}\text{As}/\text{InP}$ capacitors following an optimized $(\text{NH}_4)_2\text{S}$ treatment. Applied Physics Letters, 2011, 99, .	1.5	46
80	The Effects of Using ALD-Grown ZnO Buffer Layers on the Properties of Indium Tin Oxide Grown by Chemical Solution Deposition. Journal of Nanoscience and Nanotechnology, 2011, 11, 8354-8357.	0.9	0
81	Selected Peer-Reviewed Articles from The EuroCVD-18 Conference (EuroCVD 2011). Journal of Nanoscience and Nanotechnology, 2011, 11, 7945-7947.	0.9	0
82	A study of the electrochemical performance of vanadium oxide thin films grown by atmospheric pressure chemical vapour deposition. Solar Energy Materials and Solar Cells, 2011, 95, 2842-2847.	3.0	75
83	The effect of dopants on the morphology, microstructure and electrical properties of transparent zinc oxide films prepared by the sol-gel method. Thin Solid Films, 2011, 520, 1174-1177.	0.8	5
84	Nucleation and Chemical Transformation of RuO_2 Films Grown on (100) Si Substrates by Atomic Layer Deposition. Chemical Vapor Deposition, 2011, 17, 114-122.	1.4	14
85	Investigation of bulk defects in amorphous and crystalline HfO_2 thin films. Microelectronic Engineering, 2011, 88, 1499-1502.	1.1	7
86	The structural and electrical properties of the $\text{SrTa}_2\text{O}_6/\text{In}_{0.53}\text{Ga}_{0.47}\text{As}/\text{InP}$ system. Microelectronic Engineering, 2011, 88, 1054-1057.	1.1	7
87	The characterisation of aerosol assisted CVD conducting, photocatalytic indium doped zinc oxide films. Journal of Photochemistry and Photobiology A: Chemistry, 2011, 219, 10-15.	2.0	39
88	Electrical analysis of three-stage passivated $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ capacitors with varying HfO_2 thicknesses and incorporating an Al_2O_3 interface control layer. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2011, 29, .	0.6	31
89	Engineered Light Scattering in Colloidal Photonic Heterocrystals. Advanced Functional Materials, 2010, 20, 853-860.	7.8	18
90	The Langmuir-Blodgett Approach to Making Colloidal Photonic Crystals from Silica Spheres. Advanced Materials, 2010, 22, 3104-3124.	11.1	151

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91	Zinc oxide thin films: Characterization and potential applications. <i>Thin Solid Films</i> , 2010, 518, 4515-4519.	0.8	66
92	The incorporation of preformed metal nanoparticles in zinc oxide thin films using aerosol assisted chemical vapour deposition. <i>Thin Solid Films</i> , 2010, 518, 6921-6926.	0.8	21
93	Gallium Arsenide Infiltration of Nanoporous Multilayers: A Route to High Dielectric Contrast One-Dimensional Photonic Crystals. <i>Small</i> , 2010, 6, 1283-1287.	5.2	6
94	Structural and electrical analysis of the atomic layer deposition of HfO ₂ /In _{0.53} Ga _{0.47} As capacitors with and without an Al ₂ O ₃ interface control layer. <i>Applied Physics Letters</i> , 2010, 97, .	1.5	40
95	(Invited) Equivalent Oxide Thickness Correction in the High-k/In _{0.53} Ga _{0.47} As/InP System. <i>ECS Transactions</i> , 2010, 33, 433-444.	0.3	8
96	Structural and Electrical Analysis of Thin Interface Control Layers of MgO or Al ₂ O ₃ Deposited by Atomic Layer Deposition and Incorporated at the High-k/III-V Interface of MO ₂ /In _x Ga _{1-x} As (M = Hf Zr, x = 0 0.53) Gate Stacks. <i>ECS Transactions</i> , 2010, 33, 69-82.	0.3	9
97	Infrared and near-infrared spectroscopic probing of atomic layer deposition processes. <i>Journal of Molecular Structure</i> , 2010, 976, 324-327.	1.8	9
98	Band offsets at interfaces of (100)In _x Ga _{1-x} As (0 ≤ x ≤ 0.53) with Al ₂ O ₃ and HfO ₂ . <i>Microelectronic Engineering</i> , 2009, 86, 1550-1553.	1.1	11
99	A comparison of different spray chemical vapour deposition methods for the production of undoped ZnO thin films. <i>Thin Solid Films</i> , 2009, 518, 1129-1135.	0.8	26
100	Langmuir-Blodgett assembly of colloidal photonic crystals using silica particles prepared without the use of surfactant molecules. <i>Journal of Colloid and Interface Science</i> , 2009, 333, 816-819.	5.0	27
101	Structural analysis, elemental profiling, and electrical characterization of HfO ₂ thin films deposited on In _{0.53} Ga _{0.47} As surfaces by atomic layer deposition. <i>Journal of Applied Physics</i> , 2009, 106, 084508.	1.1	25
102	Temperature and frequency dependent electrical characterization of HfO ₂ /In _x Ga _{1-x} As interfaces using capacitance-voltage and conductance methods. <i>Applied Physics Letters</i> , 2009, 94, .	1.5	96
103	Energy barriers at interfaces between (100) In _x Ga _{1-x} As (x = 0.53) and atomic-layer deposited Al ₂ O ₃ and HfO ₂ . <i>Applied Physics Letters</i> , 2009, 94, .	1.5	24
104	Structural and Electrical Properties of HfO ₂ /In _x Ga _{1-x} As structures (x: 0,) <i>Tj ETQq0 0 0 rgBT /Overlock 10 Tf 5</i>	0.3	20
105	A comparison of the GaAs atomic layer deposition infiltration of photonic crystals engineered by the controlled evaporation and Langmuir-Blodgett methods. <i>Thin Solid Films</i> , 2008, 517, 811-813.	0.8	11
106	In situ H ₂ S passivation of In _{0.53} Ga _{0.47} As-InP metal-oxide-semiconductor capacitors with atomic-layer deposited HfO ₂ gate dielectric. <i>Applied Physics Letters</i> , 2008, 92, 022902.	1.5	49
107	Transmission spectrum transformation at photonic hetero-crystal interfaces — Polarization anisotropy. , 2008, , .		0
108	Bleaching-induced evolution of directional emission from dye-loaded opals. <i>Journal of Optics</i> , 2008, 10, 115201.	1.5	1

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109	Understanding of transmission in the range of high-order photonic bands in thin opal film. Applied Physics Letters, 2008, 92, 191106.	1.5	29
110	Energy barriers at interfaces of (100)GaAs with atomic layer deposited Al ₂ O ₃ and HfO ₂ . Applied Physics Letters, 2008, 93, .	1.5	30
111	Modification of emission of CdTe nanocrystals by the local field of Langmuir-Blodgett colloidal photonic crystals. Journal of Applied Physics, 2008, 104, 103118.	1.1	9
112	Light transmission and scattering in engineered colloidal hetero-crystals. Proceedings of SPIE, 2008, , .	0.8	0
113	In-Situ Probing of Atomic Layer Deposition Processes using Infrared and Near Infrared Spectroscopy. ECS Transactions, 2008, 16, 349-354.	0.3	5
114	Langmuir-Blodgett Approach Versus Self-Organization in Realization of Colloidal Photonic Crystals and Hetero-Crystals - Pros and Cons. , 2007, , .		0
115	Erasing diffraction orders: Opal versus Langmuir-Blodgett colloidal crystals. Applied Physics Letters, 2007, 90, 133101.	1.5	53
116	Developments in the Understanding of ALD Processes and Applications of ALD in Critical Technologies. ECS Transactions, 2007, 11, 155-166.	0.3	9
117	Optoacoustic characterization of synthetic opals. Journal of Physics: Conference Series, 2007, 92, 012030.	0.3	2
118	Atomic layer deposition for the fabrication of 3D photonic crystals structures: Growth of Al ₂ O ₃ and VO ₂ photonic crystal systems. Surface and Coatings Technology, 2007, 201, 9345-9348.	2.2	30
119	Photonic band gap thin films from mesoporous silica spheres acting as receptacles for species yielding added functionality. Photonics and Nanostructures - Fundamentals and Applications, 2007, 5, 91-95.	1.0	2
120	Novel photonic crystal thin films using the Langmuir-Blodgett approach. Physica B: Condensed Matter, 2007, 394, 233-237.	1.3	17
121	The North Atlantic Marine Boundary Layer Experiment(NAMBLEX). Overview of the campaign held at Mace Head, Ireland, in summer 2002. Atmospheric Chemistry and Physics, 2006, 6, 2241-2272.	1.9	65
122	Enhanced Bragg reflections from size-matched heterostructure photonic crystal thin films prepared by the Langmuir-Blodgett method. Applied Physics Letters, 2006, 89, 093116.	1.5	34
123	Photonic crystal thin films of GaAs prepared by atomic layer deposition. Applied Physics Letters, 2006, 89, 104103.	1.5	23
124	A broadband cavity ringdown spectrometer for in-situ measurements of atmospheric trace gases. Atmospheric Chemistry and Physics, 2005, 5, 2547-2560.	1.9	104
125	Broadband cavity ringdown spectroscopy of the NO ₃ radical. Chemical Physics Letters, 2001, 342, 113-120.	1.2	80
126	Broadband CCD detection system for rotational Raman lidar studies of the troposphere. , 2001, 4153, 657.		0

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127	The Kinetics and Mechanism of the Pyrolysis of Manganese and Manganese Silicide CVD Precursors. <i>Chemical Vapor Deposition</i> , 1998, 4, 103-107.	1.4	7
128	A broadband lidar for the measurement of tropospheric constituent profiles from the ground. <i>Journal of Geophysical Research</i> , 1998, 103, 3369-3380.	3.3	22
129	Broadband lidar measurements of tropospheric water vapor profiles. <i>Journal of Geophysical Research</i> , 1998, 103, 31191-31202.	3.3	15
130	The Kinetics and Mechanism of the Pyrolysis of Manganese and Manganese Silicide CVD Precursors. <i>Chemical Vapor Deposition</i> , 1998, 04, 103-107.	1.4	10
131	Benzoylpivaloylmethanide Precursors for the Chemical Beam Epitaxy of Oxide Thin Films. 1. Synthesis, Characterization, and Use of Yttrium Benzoylpivaloylmethanide. <i>Chemistry of Materials</i> , 1997, 9, 127-134.	3.2	5
132	Quantum beat spectroscopy of jet-cooled transient radicals generated by a pulsed electrical discharge. <i>Chemical Physics Letters</i> , 1996, 248, 470-475.	1.2	14
133	Quantum beat study of the nuclear hyperfine structure of OD and Ar ⁺ OD in their A ² Σ ⁺ electronic states. <i>Journal of Chemical Physics</i> , 1996, 104, 5365-5373.	1.2	21
134	Schiff base precursor compounds for the chemical beam epitaxy of oxide thin films. I. Deposition of CuO on MgO[001] using copper (II) bis(benzoylacetone)ethylenediimine. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1996, 14, 3208-3213.	0.9	7
135	Mechanisms of Pyrolysis of Tricarbonylcyclopentadienylmanganese and Tricarbonyl(methylcyclopentadienyl)manganese. <i>Organometallics</i> , 1995, 14, 3717-3723.	1.1	16
136	Spectroscopic Investigation of Zinc-Containing Organometallic Radicals Prepared Using a Pulsed Electrical Discharge Nozzle. <i>The Journal of Physical Chemistry</i> , 1994, 98, 10427-10431.	2.9	22
137	The use of hex-5-enylarsine as a chemically designed precursor to probe the mechanisms of the metalorganic vapour phase epitaxy growth of gallium arsenide; consequences for reactor design. <i>Journal of Crystal Growth</i> , 1994, 137, 347-354.	0.7	3
138	Do gas phase adducts form during metalorganic vapour phase epitaxial growth of gallium arsenide?. <i>Journal of Crystal Growth</i> , 1994, 145, 104-112.	0.7	12
139	Mechanisms of pyrolysis of organometallic deposition precursors. <i>Journal of Materials Chemistry</i> , 1994, 4, 13.	6.7	6
140	Decomposition of Cyanoethylphosphine, Benzylphosphine, and Cyclopentylphosphine during InP MOCVD Growth Studied by FTIR Spectroscopy: Criteria for the Design of Organophosphine Precursors. <i>Journal of the Electrochemical Society</i> , 1994, 141, 1886-1893.	1.3	5
141	Chemical vapour deposition of ZrO ₂ thin films monitored by IR spectroscopy. <i>Journal of Materials Chemistry</i> , 1994, 4, 1815.	6.7	31
142	Reflectance anisotropy from (001) GaAs surfaces during pseudo-ALE growth of GaAs. <i>Applied Surface Science</i> , 1993, 69, 46-51.	3.1	4
143	Reply to comments on "optical second harmonic generation studies of the nature of the GaAs (100) surface in the air". <i>Journal of Crystal Growth</i> , 1993, 130, 323-324.	0.7	5
144	Probing surface chemical processes during epitaxial semiconductor crystal growth at near-atmospheric pressures using photon-based techniques. <i>Faraday Discussions</i> , 1993, 95, 199.	1.6	11

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145	A RHEED and reflectance anisotropy study of the MBE growth of GaAs, AlAs and InAs on GaAs(001). Surface Science, 1992, 274, 263-269.	0.8	17
146	Optical second harmonic generation studies of the nature of the GaAs(100) surface in air. Journal of Crystal Growth, 1992, 120, 94-97.	0.7	21
147	The pyrolysis of precursors for GaAs MOCVD studied by in-situ and ex-situ Fourier transform infrared spectroscopy. Journal of Crystal Growth, 1992, 124, 10-15.	0.7	12
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